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# BAV19 / 20 / 21



DO-35 Color Band Denotes Cathode

# **Small Signal Diode**

**Absolute Maximum Ratings\*** 

 $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Value	Units	
$V_{RRM}$	Maximum Repetitive Reverse Voltage	BAV19 BAV20 BAV21	120 200 250	V V V
I <sub>F(AV)</sub>	Average Rectified Forward Current		200	mA
I <sub>FSM</sub>	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond		1.0 4.0	A A
T <sub>stg</sub>	Storage Temperature Range	-65 to +200	°C	
$T_J$	Operating Junction Temperature	175	°C	

 $<sup>{}^{\</sup>bigstar} \text{These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.}$ 

### **Thermal Characteristics**

Symbol	Parameter	Value	Units
P <sub>D</sub>	Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	°C/W

### Electrical Characteristics T<sub>4</sub> = 25°C unless otherwise noted

Symbol	Parameter		Test Conditions	Min	Max	Units
$V_R$	Breakdown Voltage	BAV19	$I_R = 100  \mu A$	120		V
		BAV20	$I_R = 100  \mu A$	200		V
		BAV21	$I_R = 100 \mu\text{A}$	250		V
V <sub>F</sub>	Forward Voltage		$I_F = 100 \text{ mA}$		1.0	V
	_		$I_F = 200 \text{ mA}$		1.25	V
I <sub>R</sub>	Reverse Current		V <sub>R</sub> = 100 V		100	nA
		BAV19	$V_R = 100 \text{ V}, T_A = 150^{\circ}\text{C}$		100	μΑ
			$V_{R} = 150 \text{ V}$		100	nA
		BAV20	$V_R = 150 \text{ V}, T_A = 150^{\circ}\text{C}$		100	μΑ
			$V_R = 200 \text{ V}$		100	nΑ
		BAV21	$V_R = 200 \text{ V}, T_A = 150^{\circ}\text{C}$		100	μΑ
C <sub>T</sub>	Total Capacitance		$V_R = 0, f = 1.0 \text{ MHz}$		5.0	pF
t <sub>rr</sub>	Reverse Recovery Time		$I_F = I_R = 30 \text{ mA}, I_{RR} = 3.0 \text{ mA},$		50	ns
			$R_L = 100\Omega$			

<sup>1)</sup> These ratings are based on a maximum junction temperature of 200 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Small Signal Diode**

(continued)

## **Typical Characteristics**

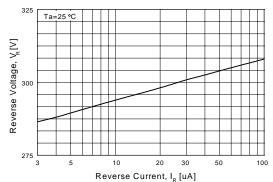
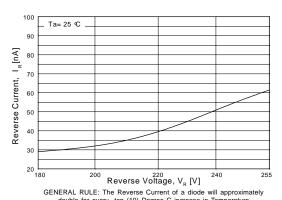


Figure 1. Reverse Voltage vs Reverse Current BV - 1.0 to 100uA



GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

Figure 3. Reverse Current vs Reverse Roltage IR - 180 to 225 V

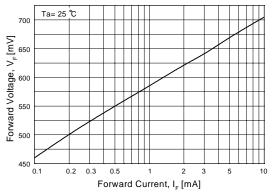


Figure 5. Forward Voltage vs Forward Current VF - 0.1 to 10mA

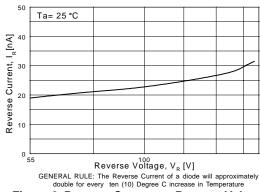


Figure 2. Reverse Current vs Reverse Voltage IR - 55 to 205 V

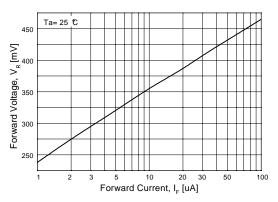


Figure 4. Forward Voltage vs Forward Current VF - 1.0 to 100uA

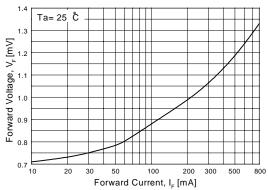


Figure 6. Forward Voltage vs Forward Current VF - 10 to 800mA

## **Small Signal Diode**

(continued)

## Typical Characteristics (continued)

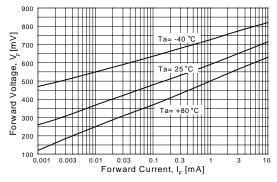


Figure 7. Forward Voltage vs Ambient Temperature VF - 1.0 uA - 10 mA (-40 to +80 Deg C)

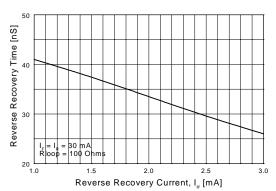


Figure 9. Reverse Recovery Time vs Reverse Recovery Current

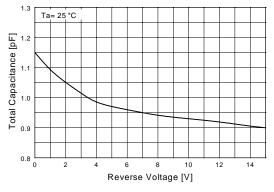


Figure 8. Total Capacitance

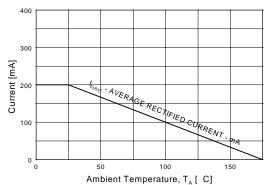


Figure 10. Average Rectified Current ( $I_{F(AV)}$ ) versus Ambient Temperature ( $T_{\Delta}$ )

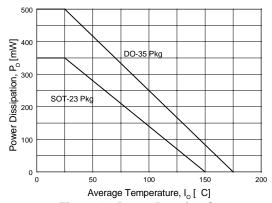


Figure 11. Power Derating Curve

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